

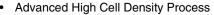


Dual P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)			
- 12	$0.037 \text{ at V}_{GS} = -4.5 \text{ V}$	- 7.7			
	0.048 at V _{GS} = - 2.5 V	- 6.8			
	0.068 at V _{GS} = - 1.8 V	- 5.7			

FEATURES

- · Halogen-free Option Available
- TrenchFET[®] Power MOSFETS: 1.8 V Rated
- New Low Thermal Resistance PowerPAK[®] Package



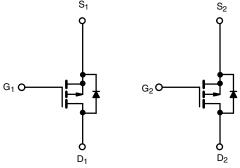
Ultra-Low R_{DS(on)}, and High P_D Capability

Pb-free

RoHS

APPLICATIONS

- Load Switch
- PA Switch
- Battery Switch
- · Bi-Directional Switch



P-Channel MOSFET

P-Channel MOSFET

PowerPAK 1212-8
3.30 mm 3.30 mm 2 3.30 mm 2 3.30 mm
Bottom View

Ordering Information: Si7909DN-T1-E3 (Lead (Pb)-free)

Si7909DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V_{DS}	- 12		V	
Gate-Source Voltage		V _{GS}	± 8			
Continuous Drain Current (T _{.I} = 150 °C) ^a	T _A = 25 °C	- I _D	- 7.7	- 5.3	A	
Continuous Diam Current (1) = 150 °C)	T _A = 85 °C		- 5.5	- 3.8		
Pulsed Drain Current		I _{DM}	- 20		A .	
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.3	- 1.1		
Marrian Danier Disabation d	T _A = 25 °C	- P _D	2.8	1.3	W	
Maximum Power Dissipation ^a	T _A = 85 °C		1.5	0.85		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations ^{b, c}			260			

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifestor to Ambrida	t ≤ 10 s	- R _{thJA}	35	44	°C/W
Maximum Junction-to-Ambient ^a	Steady State		75	94	
Maximum Junction-to-Case	Steady State	R_{thJC}	4	5	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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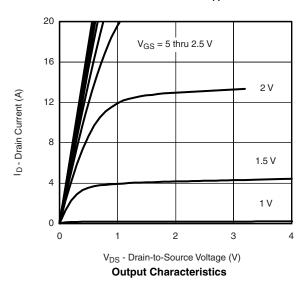
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -700 \mu A$	- 0.40		- 1.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 8 V$			± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}$	-1				
	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 85 °C			- 5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α	
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 7.7 A		0.031	0.037	Ω	
	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 6.8 A		0.040	0.048		
		V _{GS} = - 1.8 V, I _D = - 3.0 A		0.057	0.068		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 6 V, I _D = - 7.7 A		17		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 2.3 A, V _{GS} = 0 V		- 0.7	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			15.5	24		
Gate-Source Charge	Q_{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -7.7 \text{ A}$		2.5		nC	
Gate-Drain Charge	Q_{gd}			4.3			
Turn-On Delay Time	t _{d(on)}			25	40		
Rise Time	t _r	V_{DD} = - 6 V, R_L = 6 Ω		45	70		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_G = 6 Ω		90	135	ns	
Fall Time	t _f			85	130		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.3 A, dl/dt = 100 A/μs		70	110		

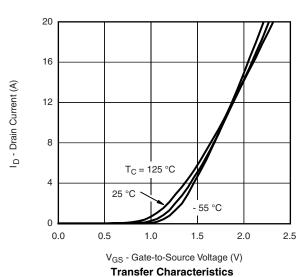
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $T_A = 25 \, ^{\circ}C$, unless otherwise noted



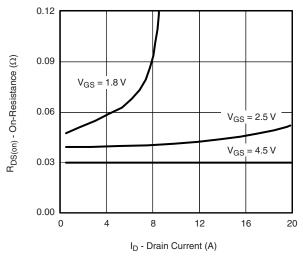




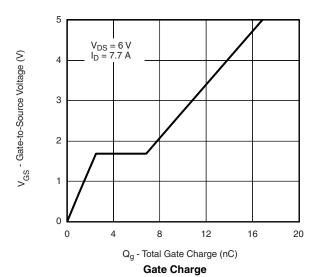


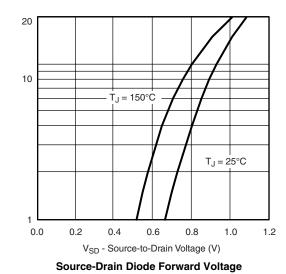


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On-Resistance vs. Drain Current





2400

1800

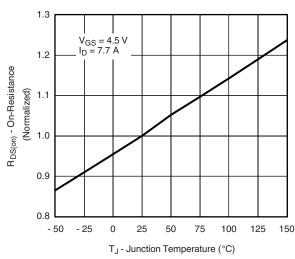
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Coss

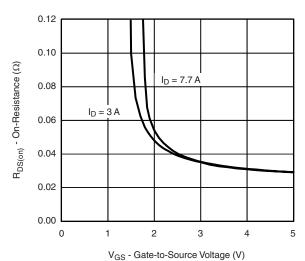
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VDS - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature



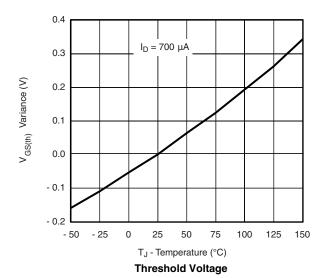
On-Resistance vs. Gate-to-Source Voltage

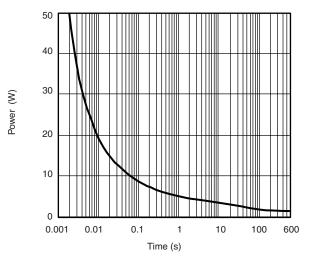
Is - Source Current (A)

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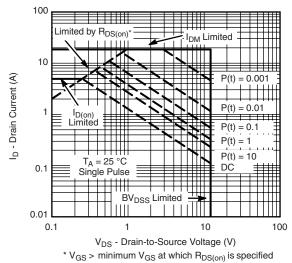
VISHAY

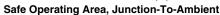
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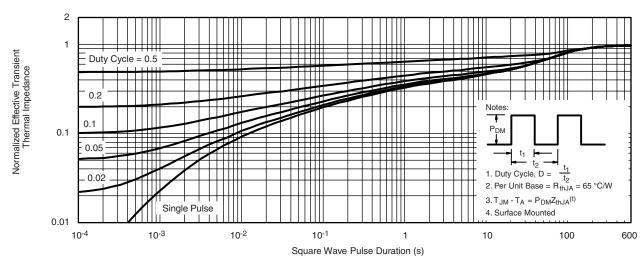




Single Pulse Power, Junction-to-Ambient



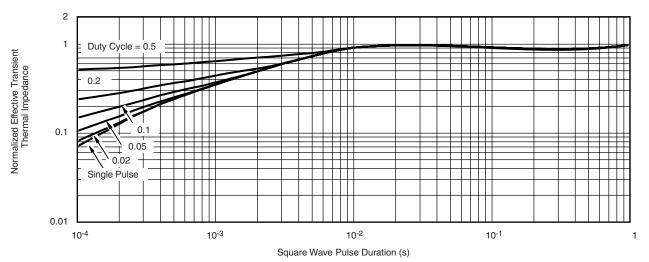




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS $T_A = 25 \, ^{\circ}C$, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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